

### Description

This bipolar junction transistor (BJT) is designed to meet the stringent requirement of automotive applications

#### **Features**

- BV<sub>CEO</sub> > 100V
- I<sub>C</sub> = 6A High Continuous Collector Current
- I<sub>CM</sub> = 10A Peak Collector Current
- P<sub>D</sub> up to 3.2W
- 43% Smaller than SOT223; 60% Smaller than TO252
- Maximum Height just 1.1mm
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DXT2011P5Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

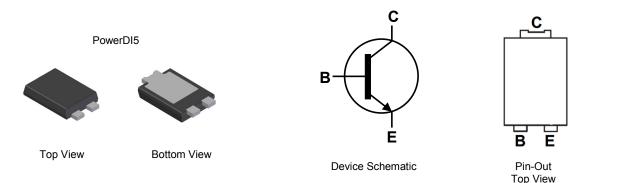
https://www.diodes.com/quality/product-definitions/

#### **Mechanical Data**

- Case: PowerDI<sup>®</sup>5
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 <sup>(3)</sup>
- Weight: 0.093 grams (Approximate)

### Applications

- Motor Drive
- Voltage Regulator Using Emitter-Follower
- DC-DC Converter
- Telecoms
- Power Management



## Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DXT2011P5Q-13	Automotive	DXT2011	13	16	5000

No purposely added lead. Fully ED Directive 2002/95/EC (ROHS), 2017/65/ED (ROHS 2) & 2015/863/ED (ROHS 3) compliant.
 See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**





DXT2011 = Product Type Marking Code D'I'= Manufacturers' Code Marking K = Factory Designator YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 19 for 2019) WW = Week Code (01 to 53)



# Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	200	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	lc	6	А
Peak Pulse Current	I <sub>CM</sub>	10	А

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.2		
Power Dissipation	(Note 6)	P <sub>D</sub>	1.7	W	
	(Note 7)		0.74		
	(Note 5)	R <sub>0JA</sub>	39	2CAN	
Thermal Resistance, Junction to Ambient Air	(Note 6)		75		
	(Note 7)		169	°C/W	
Thermal Resistance, Junction to Leads	(Note 8)	R <sub>θJL</sub>	5.6		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

## ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

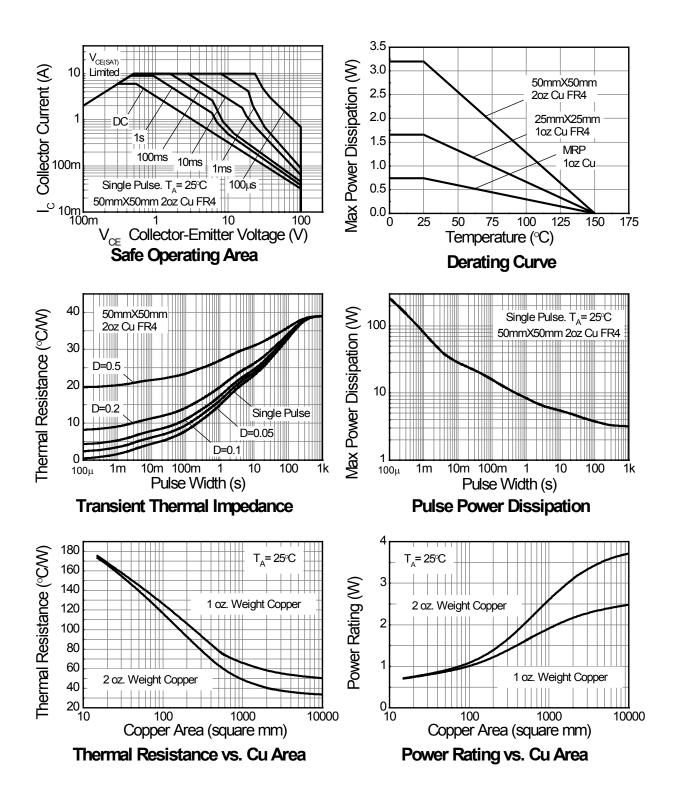
Notes: 5. For a device mounted with the exposed collector pad on 50mm × 50mm 2oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

6. Same as Note 6, except mounted on 25mm × 25mm 1oz copper.
7. Same as Note 6, except mounted on minimum recommended pad (MRP) layout.

B. Thermal resistance from junction to solder-point (on the exposed collector pad).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## **Thermal Characteristics and Derating Information**





# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

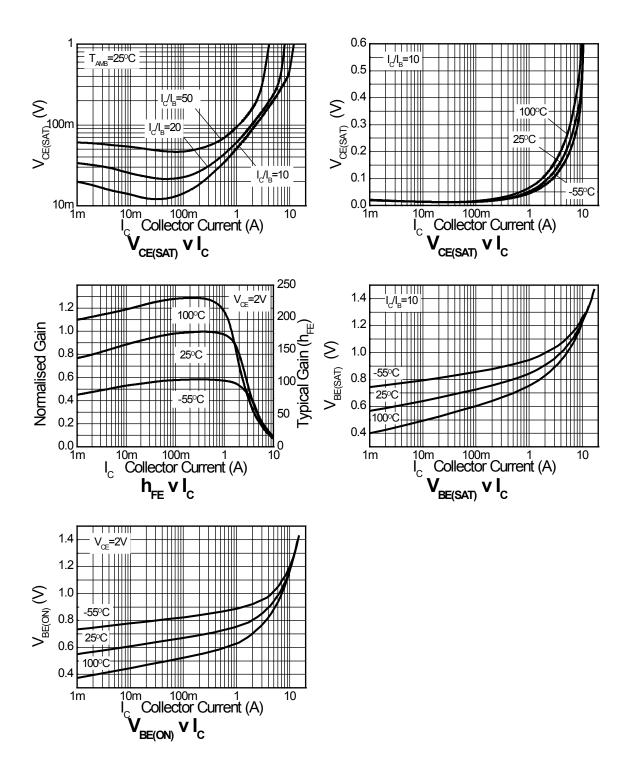
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	200	235	_	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	100	115	_	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.1	_	V	I <sub>E</sub> = 100μA
Collector Cutoff Current	I <sub>CBO</sub>		_	20 0.5	nA μA	V <sub>CB</sub> = 150V V <sub>CB</sub> = 150V, T <sub>A</sub> = +100°C
Collector Cutoff Current	I <sub>CER</sub> R≤1kΩ		_	20 0.5	nA μA	V <sub>CB</sub> = 150V V <sub>CB</sub> = 150V, T <sub>A</sub> = +100°C
Emitter Cutoff Current	I <sub>EBO</sub>	_	_	10	nA	V <sub>EB</sub> = 6V
Collector-Emitter Saturation Voltage (Note 10)	V <sub>CE(sat)</sub>		21 50 95 180	35 65 125 220	mV	$I_{C} = 0.1A, I_{B} = 5mA$ $I_{C} = 1A, I_{B} = 100mA$ $I_{C} = 2A, I_{B} = 100mA$ $I_{C} = 5A, I_{B} = 500mA$
Base-Emitter Saturation Voltage (Note 10)	V <sub>BE(sat)</sub>	_	1020	1120	mV	I <sub>C</sub> = 5A, I <sub>B</sub> = 500mA
Base-Emitter Turn-On Voltage (Note 10)	V <sub>BE(on)</sub>	_	920	1000	mV	$V_{CE} = 2V, I_C = 5A$
DC Current Gain (Note 10)	h <sub>FE</sub>	100 100 30 10		 300 		$V_{CE} = 2V, I_C = 10mA$ $V_{CE} = 2V, I_C = 2A$ $V_{CE} = 2V, I_C = 5A$ $V_{CE} = 2V, I_C = 10A$
Transition Frequency	f⊤		130	_	MHz	V <sub>CE</sub> = 10V, I <sub>C</sub> = 100mA, f = 50MHz
Output Capacitance	C <sub>obo</sub>	_	26	_	pF	V <sub>CB</sub> = 10V, f = 1MHz
Switching Times	t <sub>on</sub> t <sub>off</sub>	_	41 1010	_	ns	$V_{CC} = 10V, I_C = 1A,$ $I_{B1} = -I_{B2} = 100mA$

Note: 10. Pulse Test: Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2.0%.



DXT2011P5Q

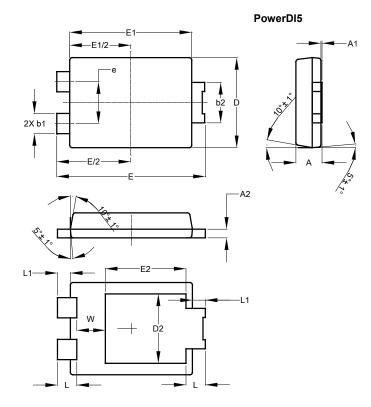
## Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





# Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

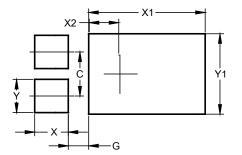


PowerDI5					
Dim	Min	Max	Тур		
Α	1.05	1.15	1.10		
A1	0.00	0.05			
A2	0.33	0.43	0.381		
b1	0.80	0.99	0.89		
b2	1.70	1.88	1.78		
D	3.90	4.05	3.966		
D2			3.054		
Е	6.40	6.60	6.51		
е			1.84		
E1	5.30	5.45	5.37		
E2		-	3.549		
L	0.75	0.95	0.85		
L1	0.50	0.65	0.57		
W	1.10	1.41	1.255		
All	All Dimensions in mm				

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5



Dimensions	Value (in mm)
С	1.840
G	0.852
Х	1.400
X1	4.860
X2	1.310
Y	1.390
Y1	3.360

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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